

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

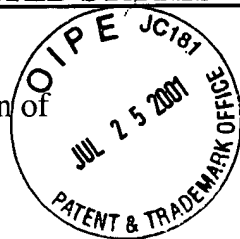
In re Patent Application of

Wendong ZHEN

Serial No. 09/842,631

Filed: April 27, 2001

For: SEMICONDUCTOR DEVICE HAVING FERROELECTRIC THIN FILM AND  
FABRICATING METHOD THEREFOR



Atty. Ref.: 925-192

Group: 2815

Examiner: unknown

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~~Dep & Ref~~  
302  
6/1/01  
J. Steptoe  
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Assistant Commissioner for Patents  
Washington, DC 20231

Sir:

**PRELIMINARY AMENDMENT**

RECEIVED  
OCT - 4, 2001  
TC 2800 MAIL ROOM

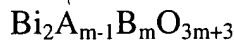
In order to place the above-identified application in better condition for  
examination, please amend the application as follows:

**IN THE CLAIMS**

Please substitute the following amended claim 27 for corresponding claim 27  
previously presented. A copy of the amended claim showing current revisions is  
attached.

27. {AMENDED} A semiconductor device fabricating method as claimed in claim  
25, wherein

the ferroelectric thin film is made of a material expressed by:



where A represents one selected from a group consisting of Na, K, Pb, Ca, Sr, Ba and Bi,  
B represents one selected from a group consisting of Fe, Ti, Nb, Ta, W and Mo, and m  
represents a natural number.